

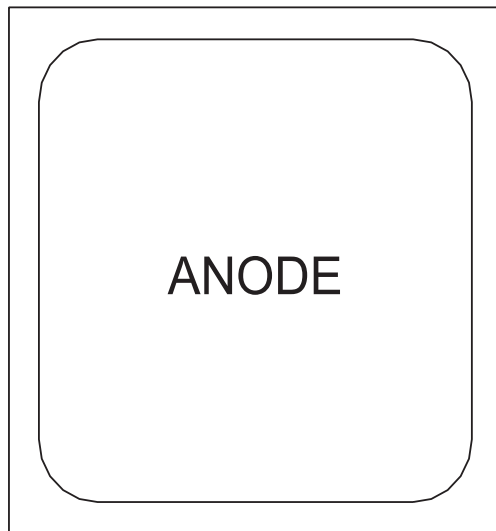
PROCESS CPD06
General Purpose Rectifier
3 Amp Glass Passivated Rectifier Chip



PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	89 x 89 MILS
Die Thickness	10.2 MILS
Anode Bonding Pad Area	66 x 66 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

1,490

PRINCIPAL DEVICE TYPES

1N5400 thru 1N5408

1N5550 thru 1N5554

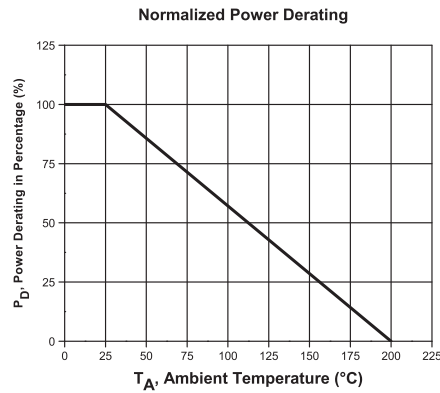
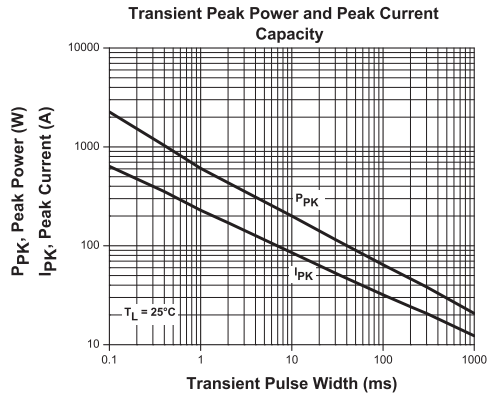
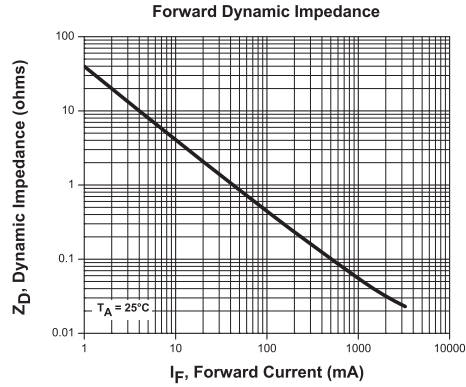
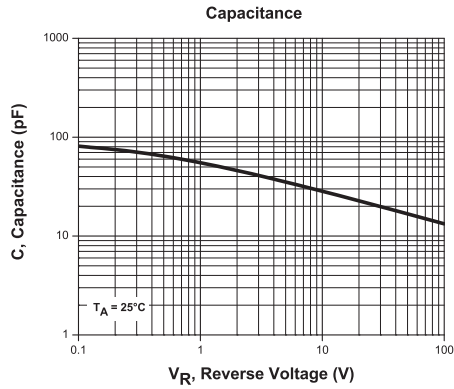
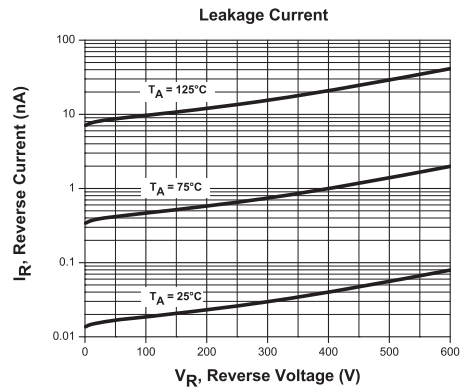
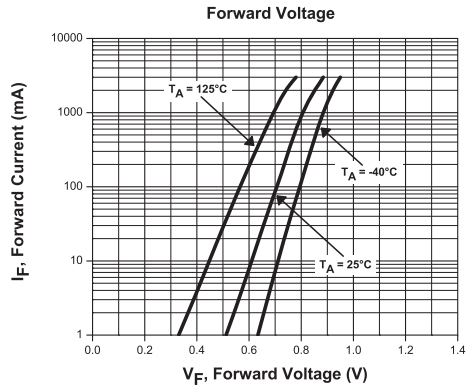
1N5624 thru 1N5627

CMR3-02 Series

R4 (22-March 2010)

PROCESS CPD06

Typical Electrical Characteristics



R4 (22-March 2010)